

### MG1275S-BA1MM



#### Features

- Ultra Low Loss
- High Ruggedness
- High Short Circuit Capability
- Positive Temperature Coefficient
- With Fast Free-Wheeling Diodes

#### Applications

- Inverter
- Converter
- Welder
- SMPS and UPS
- Induction Heating

#### Agency Approvals

AGENCY	AGENCY FILE NUMBER
	E71639

#### Module Characteristics ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
$R_{thJC}$	Junction-to-Case Thermal Resistance	Per IGBT			0.2	K/W
$R_{thJD}$		Per Inverse Diode			0.5	K/W
Torque	Module-to-Sink	Recommended (M6)	3		5	N-m
Torque	Module Electrodes	Recommended (M5)	2.5		5	N-m
Weight				150		g

#### Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Parameters	Test Conditions	Values	Unit
<b>IGBT</b>				
$V_{CES}$	Collector - Emitter Voltage		1200	V
$V_{GES}$	Gate - Emitter Voltage		$\pm 20$	V
$I_c$	DC Collector Current	$T_c=25^\circ\text{C}$	105	A
		$T_c=80^\circ\text{C}$	75	A
$I_{cpuls}$	Pulsed Collector Current	$T_c=25^\circ\text{C}, t_p=1\text{ms}$	210	A
		$T_c=80^\circ\text{C}, t_p=1\text{ms}$	150	
$P_{tot}$	Power Dissipation Per IGBT		630	W
$T_J$	Junction Temperature Range		-40 to +150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range		-40 to +125	$^\circ\text{C}$
$V_{isol}$	Insulation Test Voltage	AC, $t=1\text{min}$	3000	V
<b>Diode</b>				
$V_{RRM}$	Repetitive Reverse Voltage		1200	V
$I_{F(AV)}$	Average Forward Current	$T_c=25^\circ\text{C}$	90	A
		$T_c=80^\circ\text{C}$	60	A
$I_{F(RMS)}$	RMS Forward Current		90	A
$I_{FSM}$	Non-Repetitive Surge Forward Current	$T_J=45^\circ\text{C}, t=10\text{ms}$ , Sine	430	A
		$T_J=45^\circ\text{C}, t=8.3\text{ms}$ , Sine	450	

Life Support Note:

#### Not Intended for Use in Life Support or Life Saving Applications

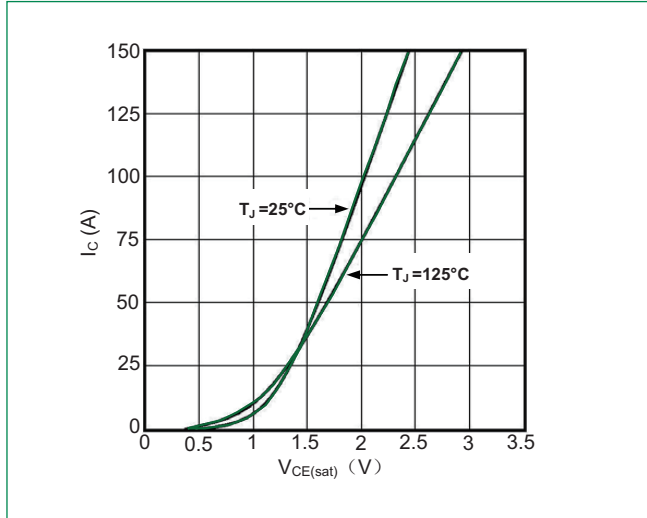
The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

MG1275S-BA1MM

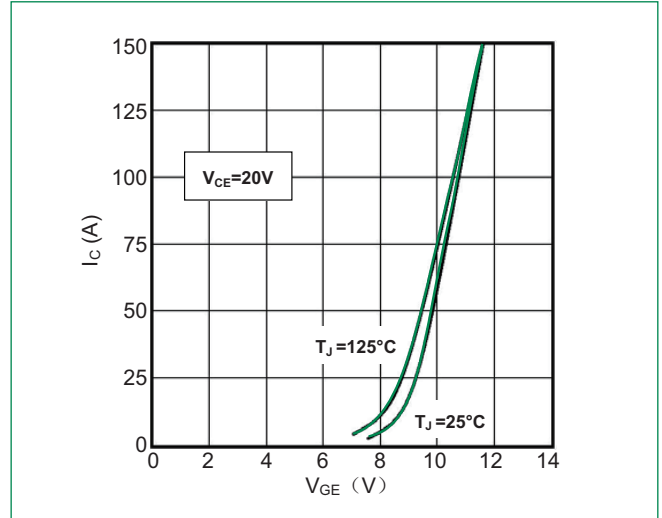
### Electrical and Thermal Specifications ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit	
<b>IGBT</b>							
$V_{GE(th)}$	Gate - Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=3\text{mA}$	5.0	6.2	7.0	V	
$V_{CE(sat)}$	Collector - Emitter Saturation Voltage	$I_C=75\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		1.8		V	
		$I_C=75\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		2.0		V	
$I_{CES}$	Collector Leakage Current	$V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		0.2	0.5	mA	
		$V_{CE}=1200\text{V}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		2		mA	
$I_{GES}$	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}$	-100		100	nA	
$Q_{ge}$	Gate Charge	$V_{CC}=600\text{V}, I_C=75\text{A}, V_{GE}=\pm 15\text{V}$		780		nC	
$C_{ies}$	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		5.52		nF	
$C_{oes}$	Output Capacitance			0.4			
$C_{res}$	Reverse Transfer Capacitance			0.26			
$t_{d(on)}$	Turn - on Delay Time	$V_{CC}=600\text{V}$ $I_C=75\text{A}$ $R_G=15\Omega$ $V_{GE}=\pm 15\text{V}$ Inductive Load	$T_J=25^\circ\text{C}$		150		ns
			$T_J=125^\circ\text{C}$		160		ns
$t_r$	Rise Time		$T_J=25^\circ\text{C}$		65		ns
			$T_J=125^\circ\text{C}$		65		ns
$t_{d(off)}$	Turn - off Delay Time		$T_J=25^\circ\text{C}$		440		ns
			$T_J=125^\circ\text{C}$		500		ns
$t_f$	Fall Time		$T_J=25^\circ\text{C}$		55		ns
			$T_J=125^\circ\text{C}$		70		ns
$E_{on}$	Turn - on Energy		$T_J=25^\circ\text{C}$		7.45		mJ
			$T_J=125^\circ\text{C}$		10.3		mJ
$E_{off}$	Turn - off Energy	$T_J=25^\circ\text{C}$		4.9		mJ	
		$T_J=125^\circ\text{C}$		7.8		mJ	
<b>Diode</b>							
$V_F$	Forward Voltage	$I_F=75\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		2.0	2.48	V	
		$I_F=75\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1.7	2.2	V	
$t_{rr}$	Reverse Recovery Time	$I_F=75\text{A}, V_R=800\text{V}$ $di_F/dt=-1000\text{A}/\mu\text{s}$ $T_J=125^\circ\text{C}$		200		ns	
$I_{RRM}$	Max. Reverse Recovery Current			70		A	
$Q_{rr}$	Reverse Recovery Charge			8.2		$\mu\text{C}$	

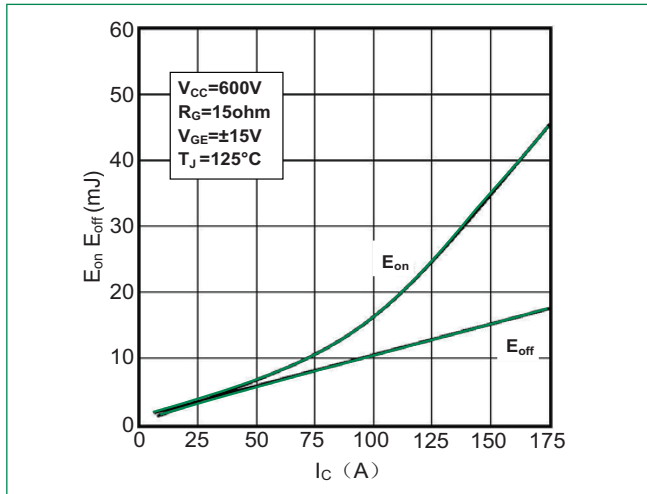
**Figure 1: Typical Output Characteristics**



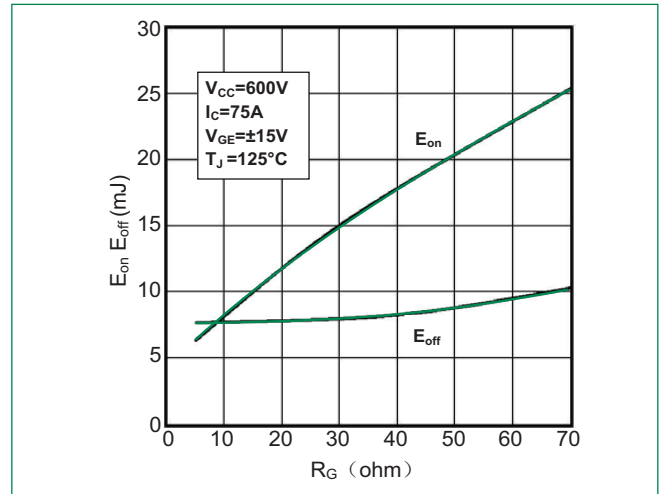
**Figure 2: Typical Transfer characteristics**



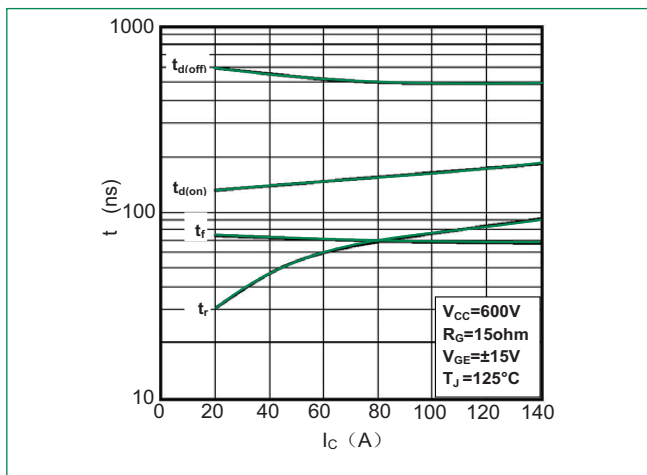
**Figure 3: Switching Energy vs. Collector Current**



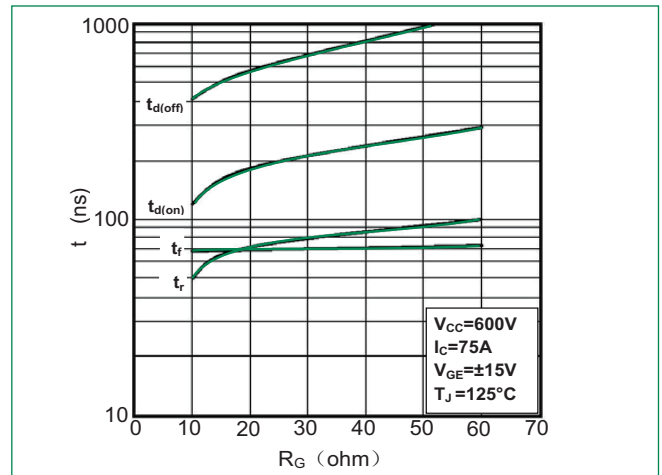
**Figure 4: Switching Energy vs. Gate Resistor**



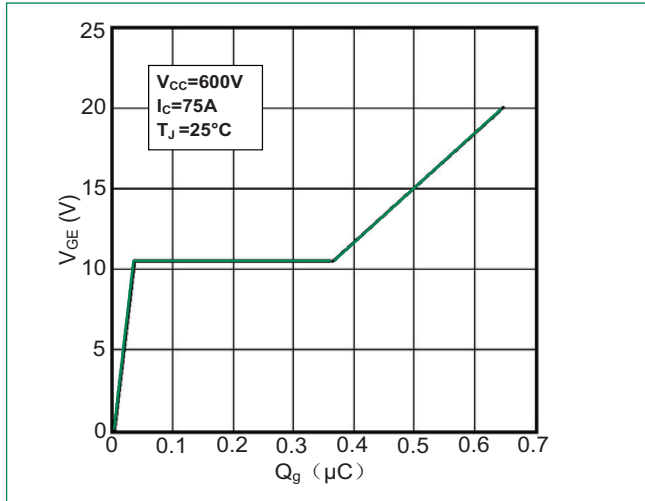
**Figure 5: Switching Times vs. Collector Current**



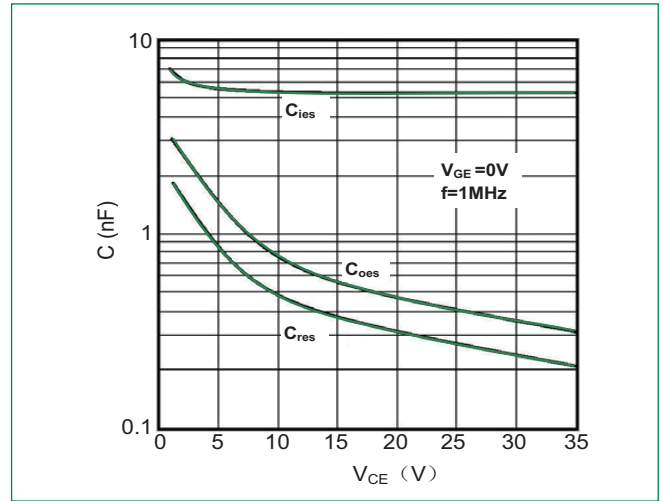
**Figure 6: Switching Times vs. Gate Resistor**



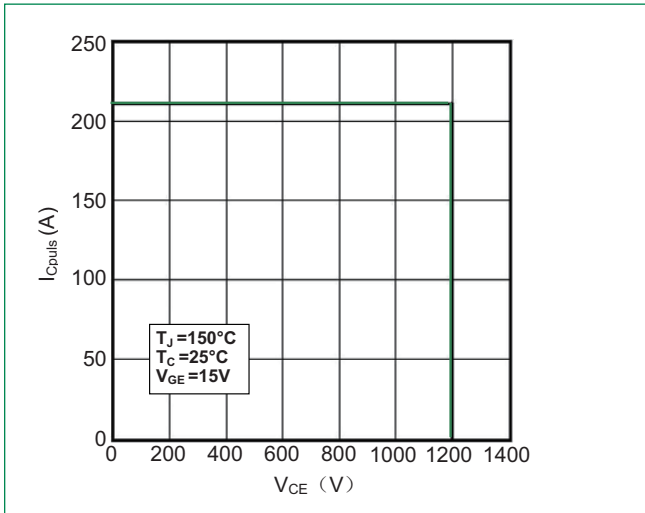
**Figure 7: Gate Charge characteristics**



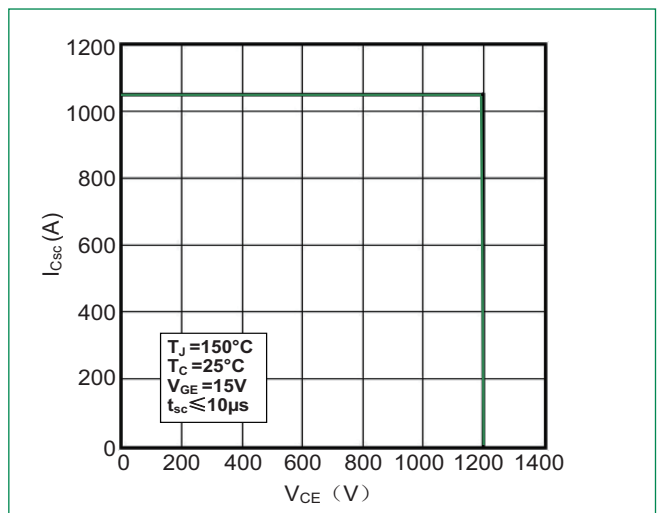
**Figure 8: Typical Capacitances vs.  $V_{CE}$**



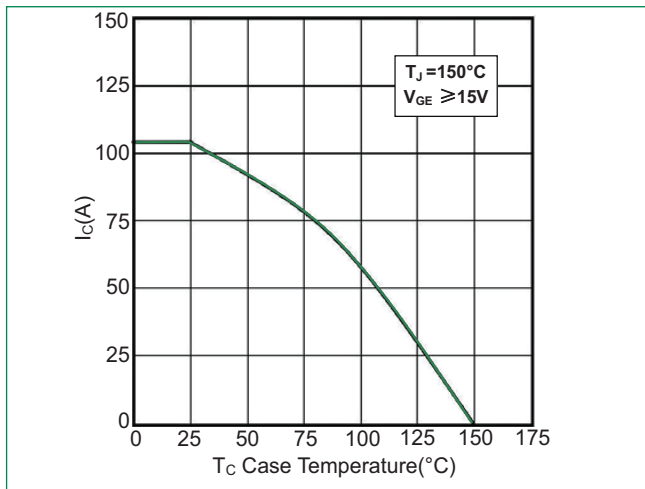
**Figure 9: Reverse Biased Safe Operating Area**



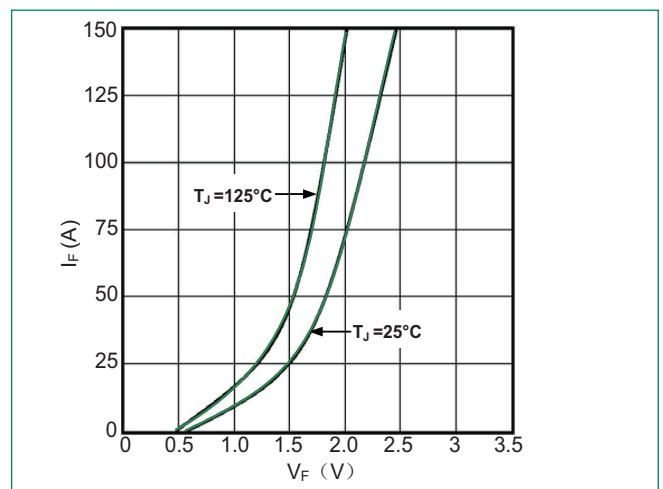
**Figure 10: Short Circuit Safe Operating Area**



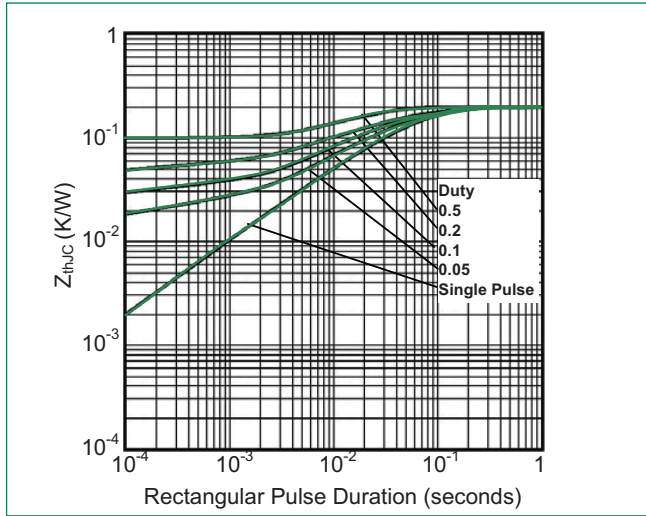
**Figure 11: Rated Current vs.  $T_C$**



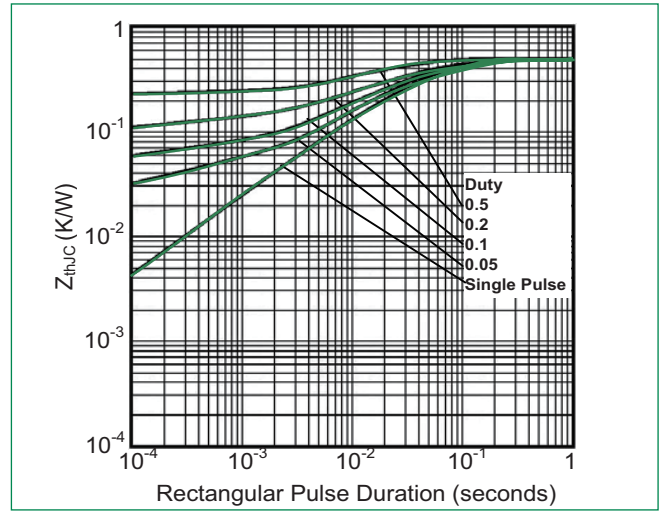
**Figure 12: Diode Forward Characteristics**



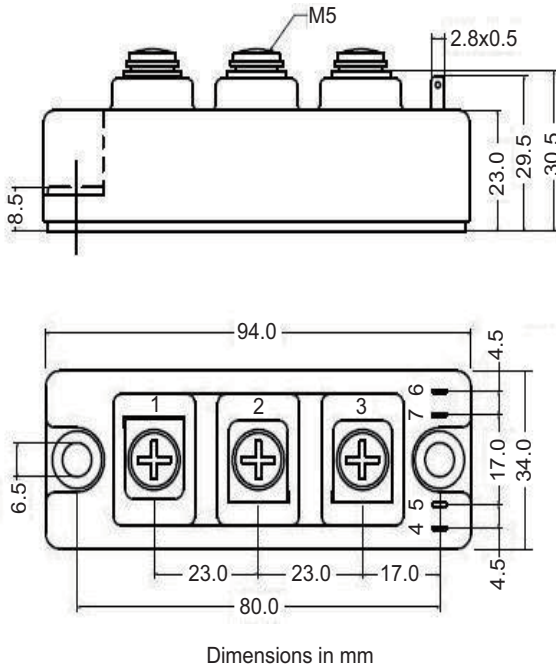
**Figure 13: Transient Thermal Impedance of IGBT**



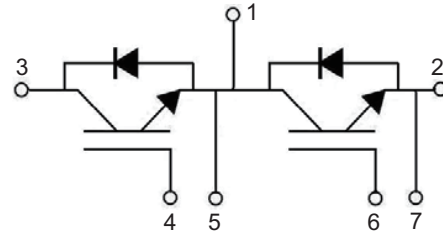
**Figure 14: Transient Thermal Impedance of Diode**



**Dimensions-Package S**



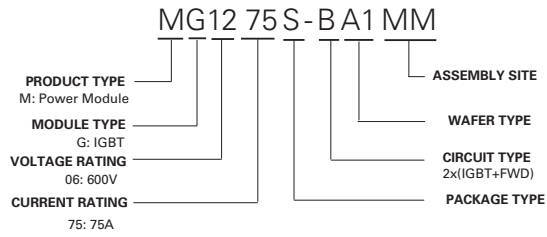
**Circuit Diagram**



### Packing Options

Part Number	Marking	Weight	Packing Mode	M.O.Q
MG1275S-BA1MM	MG1275S-BA1MM	150g	Bulk Pack	100

### Part Numbering System



### Part Marking System

